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Should be replaced with:

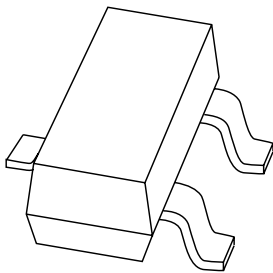
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DATA SHEET



## **BSS63** PNP high-voltage transistor

Product data sheet  
Supersedes data of 1999 Apr 15

2004 Jan 16

# PNP high-voltage transistor

# BSS63

### FEATURES

- Low current (max. 100 mA)
- High voltage (max. 100 V).

### APPLICATIONS

- High-voltage general purpose
- Switching applications.

### DESCRIPTION

PNP high-voltage transistor in a SOT23 plastic package.  
NPN complement: BSS64.

### MARKING

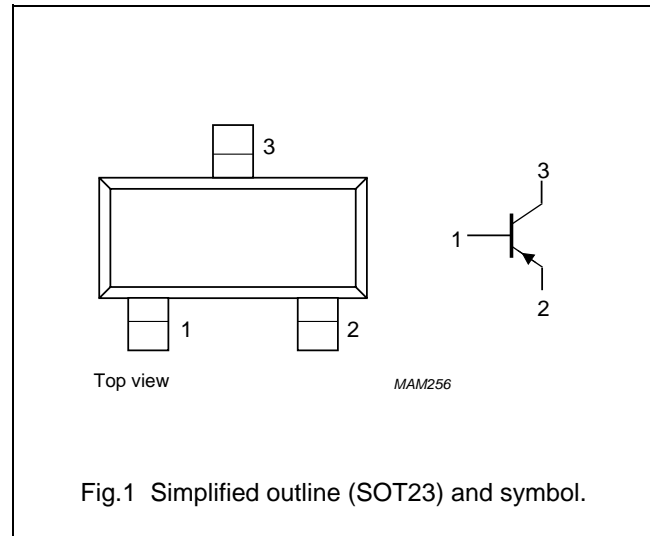
| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| BSS63       | BM*                         |

### Note

- \* = p : Made in Hong Kong.  
\* = t : Made in Malaysia.  
\* = W : Made in China.

### PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |



### ORDERING INFORMATION

| TYPE NUMBER | PACKAGE |  |         |
|-------------|---------|--|---------|
|             | NAME    | DESCRIPTION                              | VERSION |
| BSS63       | -       | plastic surface mounted package; 3 leads | SOT23   |

## PNP high-voltage transistor

BSS63

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL    | PARAMETER                     | CONDITIONS                              | MIN. | MAX. | UNIT             |
|-----------|-------------------------------|---|------|------|------------------|
| $V_{CBO}$ | collector-base voltage        | open emitter                            | –    | –110 | V                |
| $V_{CEO}$ | collector-emitter voltage     | open base                               | –    | –100 | V                |
| $V_{EBO}$ | emitter-base voltage          | open collector                          | –    | –6   | V                |
| $I_C$     | collector current (DC)        |   | –    | –100 | mA               |
| $I_{CM}$  | peak collector current        |   | –    | –100 | mA               |
| $I_{BM}$  | peak base current             |   | –    | –100 | mA               |
| $P_{tot}$ | total power dissipation       | $T_{amb} \leq 25\text{ }^\circ\text{C}$ | –    | 250  | mW               |
| $T_{stg}$ | storage temperature           |   | –65  | +150 | $^\circ\text{C}$ |
| $T_j$     | junction temperature          |   | –    | 150  | $^\circ\text{C}$ |
| $T_{amb}$ | operating ambient temperature |   | –65  | +150 | $^\circ\text{C}$ |

**THERMAL CHARACTERISTICS**

| SYMBOL        | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------|---|------------|-------|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | note 1     | 500   | K/W  |

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**CHARACTERISTICS** $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

| SYMBOL      | PARAMETER                            | CONDITIONS  | MIN. | TYP. | MAX. | UNIT          |
|-------------|--------------------------------------|---|------|------|------|---------------|
| $I_{CBO}$   | collector cut-off current            | $I_E = 0; V_{CB} = -90\text{ V}$                                  | –    | –    | –100 | nA            |
|             |                                      | $I_E = 0; V_{CB} = -90\text{ V}; T_j = 150\text{ }^\circ\text{C}$ | –    | –    | –50  | $\mu\text{A}$ |
| $I_{EBO}$   | emitter cut-off current              | $I_C = 0; V_{EB} = -6\text{ V}$                                   | –    | –    | –100 | nA            |
| $h_{FE}$    | DC current gain                      | $I_C = -10\text{ mA}; V_{CE} = -1\text{ V}$                       | 30   | –    | –    |               |
|             |                                      | $I_C = -25\text{ mA}; V_{CE} = -1\text{ V}$                       | 30   | –    | –    |               |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = -25\text{ mA}; I_B = -2.5\text{ mA}$                       | –    | –    | –250 | mV            |
| $V_{BEsat}$ | base-emitter saturation voltage      | $I_C = -25\text{ mA}; I_B = -2.5\text{ mA}$                       | –    | –    | –900 | mV            |
| $C_c$       | collector capacitance                | $I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$          | –    | 3    | –    | pF            |
| $f_T$       | transition frequency                 | $I_C = -25\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$   | 50   | 85   | –    | MHz           |

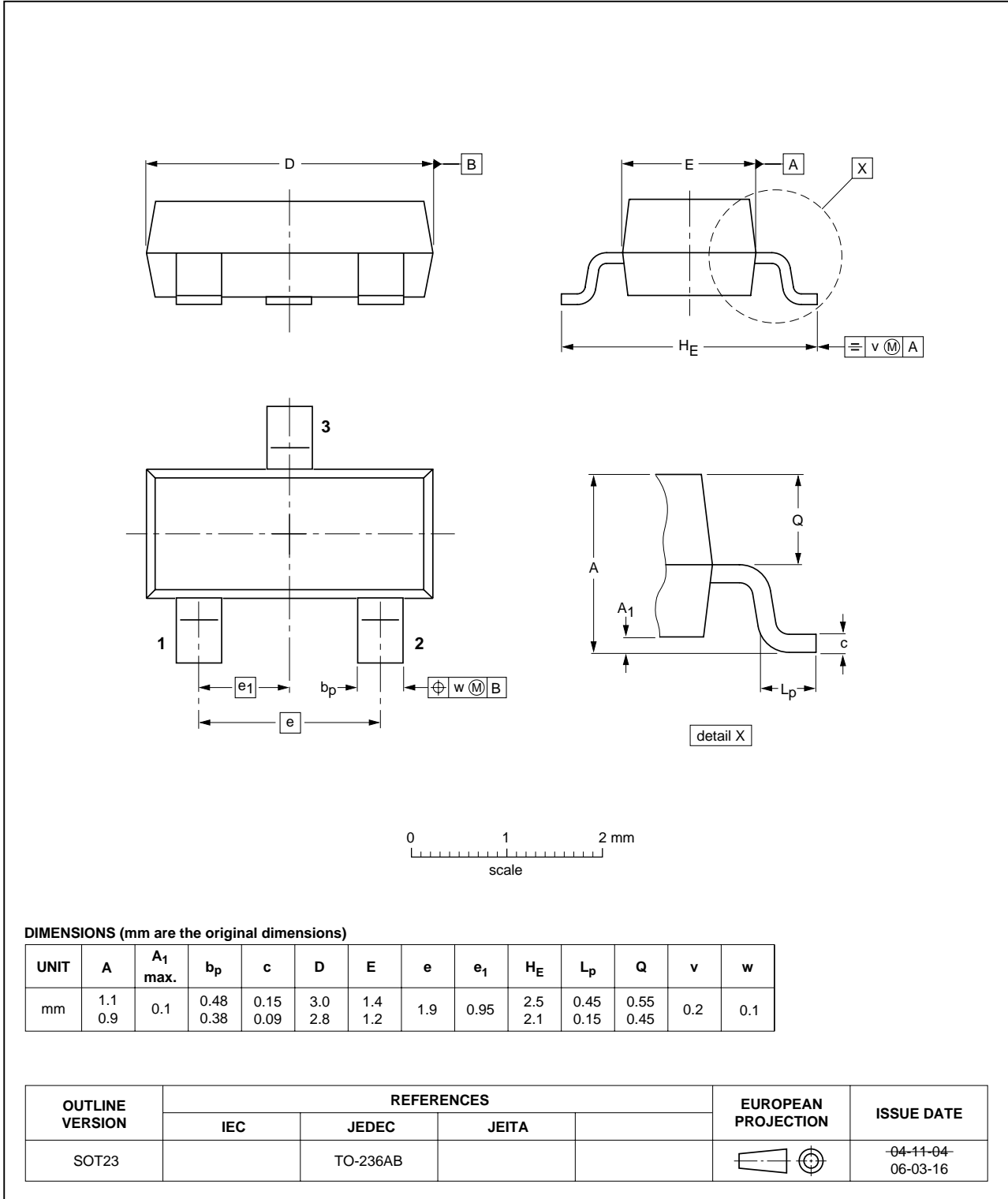
PNP high-voltage transistor

BSS63

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



PNP high-voltage transistor

BSS63

DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

Notes

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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